

Effect of Deposition Potential on Lead Sulphide (PbS) Semiconductor Thin Deposited by Electrodeposition Technique

ABSTRACT

This current paper studied the effect of variations in deposition voltage on lead sulphide (PbS) thin film, using electrodeposition technique, with zinc plate as substrate. The result showed an inverse relationship between voltage and the thickness of the film. An inverse relationship between film's thickness and its resistivity was also obvious. For given values of voltage, the dependence of absorbance, transmittance and reflectance of the film on the wavelength of the incident radiation was observed. The absorbance and reflectance were found to exhibit an inverse relationship with the wavelength. However, the transmittance was observed to increase as the wavelength is increased. The highest transmittance of 0.716% in the infrared region at the wavelength of 300nm was recorded for all samples deposited at 1V. In the ultraviolet region, a transmittance of 0.946% at incident wavelength of 1500nm for all samples deposited at 5V was recorded. From the result analysis, it was observed that the reflection index, optical conductivity, extinction coefficient, real dielectric constant, and imaginary dielectric constant increased as the photon energy. The observe energy band gap of 1.7eV-2.4eV shows that PbS can be used as photovoltaic cell.

Keywords: Thin films, PbS, Electrodeposition and optical analysis

1.0 Introduction

Semiconductor thin films of IV–VI have been studied due to their potential application in solar cells and sensors. Lead sulphide (PbS) is a very important direct narrow gap binary semiconducting material with relatively large excitation Bohr radius of 18nm [1]. This is the very important property for the applications of infrared detection [2]. This PbS is also used in variety of applications such as ion-selective sensors, solar absorption, solar control coatings and diode lasers [3-10]. Due to its physical properties, PbS is considered a prime candidate for a photovoltaic(PV) material and has generated great interest in its use. The PbS material is characterized by a direct band gap (1.5eV) with a high absorption coefficient. Another great advantage of PbS is that it can be deposited by number of techniques including evaporation, sublimation, sputtering and chemical methods. The growth of PbS films by electrodeposition is a simple and low cost process of producing high-quality material for PV device fabrication. Thin film PbS has attracted a great deal of interest for low-cost, high-efficiency photovoltaic energy conversion applications [11]. Among the various techniques that are available for PbS thin film deposition, electrodeposition, a non-vacuum technique, has the advantage of low cost, efficient utilization of raw material, and scalability for high-

40 volume production. At the same time, additional research is still needed to improve upon the
 41 process reproducibility and performance levels achieved to date. Among the significant issues
 42 are interface carrier recombination and top-layer photon absorption which presently limit the
 43 short circuit current, junction recombination which limits the open-circuit voltage, and series-
 44 resistance losses which suppress the fill-factor [8]. In this research paper, we are interested in
 45 the deposited of PbS thin films semiconductor by looking at the effect of deposition potential
 46 on the electrical and optical properties of the material deposited.

47 2.0 Materials and Methods

48 The experimental analysis of PbS thin films was carried out using lead Nitrate $\text{Pb}(\text{NO}_3)_2$,
 49 Sodium Sulphate Anhydrous (Na_2SO_4), Potassium tetraoxosulphate VI (K_2SO_4) and
 50 H_2SO_4 . Deposition potential (voltages) was varied and the growth of PbS films and
 51 others bath parameter were determined with respect to the different bath parameters
 52 which includes time of deposition and substrate for the deposition. The concentration
 53 of the solution were kept constant throughout the experiment. The concentration of the
 54 compounds was maintained as prepared. The following are the concentration of the
 55 concentration of the substance prepared: 0.1M $\text{Pb}(\text{NO}_3)_2$, 0.1M Na_2SO_4 , 0.092M K_2SO_4
 56 and 0.1M H_2SO_4 . A volume of 20cm^3 each of $\text{Pb}(\text{NO}_3)_2$ and Na_2SO_4 was
 57 measured into 150ml beaker using burette. A volume of 10cm^3 of K_2SO_4 was measured
 58 into the same 150ml beaker containing $\text{Pb}(\text{NO}_3)_2$ and Na_2SO_4 respectively to serve as
 59 the inert electrolyte which helps to dissociate the Pb from the $\text{Pb}(\text{NO}_3)_2$ and S from
 60 the Na_2SO_4 to form the required PbS film on the substrate. Finally, 5cm^3 of H_2SO_4
 61 was added to acidified the solution. The entire mixture was stirred with the glass rod to
 62 achieve uniformity. In each of the reaction baths prepared, a metal substrate (Zinc
 63 plate) and carbon electrode were connected to a DC power supply source and the
 64 voltage was maintained at 7V. The absorbance was measured using M501 UV-visible
 65 spectrophotometer in the wavelength range of 300-1500nm and other solid state properties
 66 were calculated. The electrical (I/V) was obtained using four point probe (Model T345) and
 67 the resistivity and conductivity were calculated for various thickness.

68 **Table 1: Variation of Parameters PbS Thin films**

Samples	Volume of $\text{Pb}(\text{NO}_3)_2$	Volume of Na_2SO_4	Volume of K_2SO_4	Volume of H_2SO_4	Voltage(V)	Time(s)
LS1	20.00	20.00	10.00	5.00	1.00	60.00

LS2	20.00	20.00	10.00	5.00	2.00	60.00
LS3	20.00	20.00	10.00	5.00	3.00	60.00
LS4	20.00	20.00	10.00	5.00	4.00	60.00
LS5	20.00	10.00	10.00	5.00	5.00	60.00

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Results and Discussions

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3.1 Electrical analysis of PbS thin films

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The electrical (I/V) characterization analysis was carried out using a four point probe instrument (Model-T345), where the sheet resistivity and conductivity of the films were studied. The arrangement was made in such a way that the voltage across the transverse distance of the films and the values of the current were measured using silver paste to ensure good ohmic contact to the film. The calculated results for the sheet resistivity and electrical conductivity with their corresponding time and thickness are shown Table 1. The results showed that PbS thin films resistivity increases as the voltage increases and conductivity of the material increases as the thickness of the material decreases. The high resistivity and low conductivity of the deposited films makes the material suitable for mass production of PV solar panel and other electronics devices. It is a semiconductor that has large potential applications in thin films technology like photo luminescence and electroluminescent devices [9-10]

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Table 2: Electrical properties of PbS thin films

SAMPLES	VOLTAGE (V)	THICKNESS, t (nm)	RESISTIVITY, ρ (Ωm)	CONDUCTIVITY, σ (Ωm) ⁻¹
LS1	1.00	386	5.345×10^{-2}	1.870×10^{-2}
LS2	2.00	355	4.456×10^{-2}	2.244×10^{-2}
LS3	3.00	321	3.324×10^{-2}	3.008×10^{-2}
LS4	4.00	211	2.451×10^{-2}	4.079×10^{-2}
LS5	5.00	190	1.398×10^{-2}	7.153×10^{-2}

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3.2 Optical analysis of PbS thin films

Figure 1 shows the plot of absorbance as a function of wavelength of PbS thin films deposited at different potential at constant time (60s). From the graph, it was observed that as the wavelength of the films radiation increases the absorbance of the films decreases. From Fig. 1, it was noticed that samples deposited at 5V recorded the value of 0.249 which is the highest value of absorbance at a wavelength incidence of 360nm while Sample deposited at 1V was found to recorded lowest absorption value of 0.149 at incidence wavelength of 300nm and sample deposited at 4V tend to maintained a steady increase which recorded the absorption value of 0.235 at incidence wavelength of 320nm. However, absorbance of the films was found to be low in the both regions [12, 9-10].

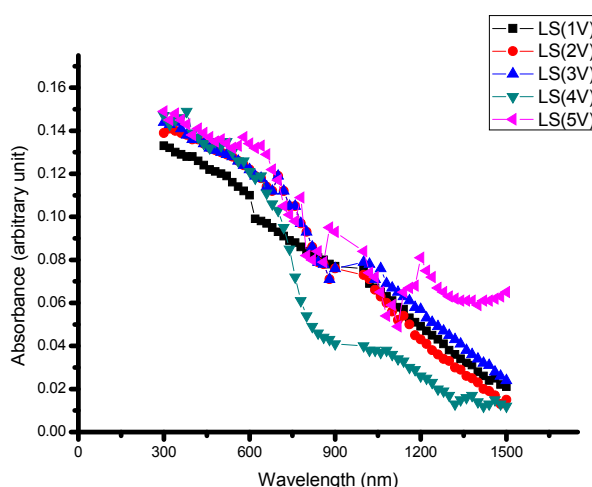
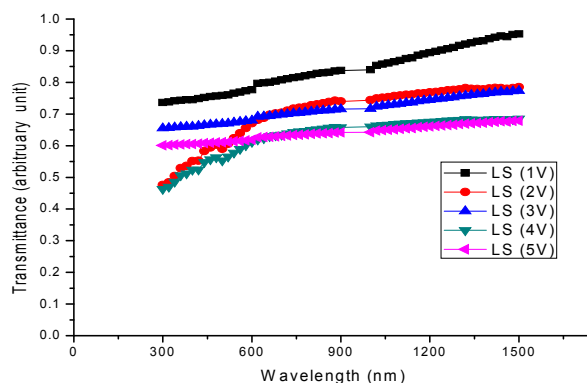


Figure 1: plot of absorbance as a function wavelength

Figure 2 shows the plot transmittance (%) as a function of wavelength of PbS thin films deposited at different potential at constant time (60s). From the graph, it was observed that the wavelength of incident radiation increases as the transmittance increases. From the graph, it was noticed that all the samples deposited at different time interval followed the same trend. It was also observed that sample deposited at 1V recorded the highest transmittance of 0.716% in the infrared region at incidence wavelength of 300nm and transmittance of about 0.946% in the ultraviolet region at incidence wavelength of 1500nm. The sample deposited at 5V recorded the lowest transmittance. However, all the samples deposited recorded transmittance above 50%. [12, 9-10].

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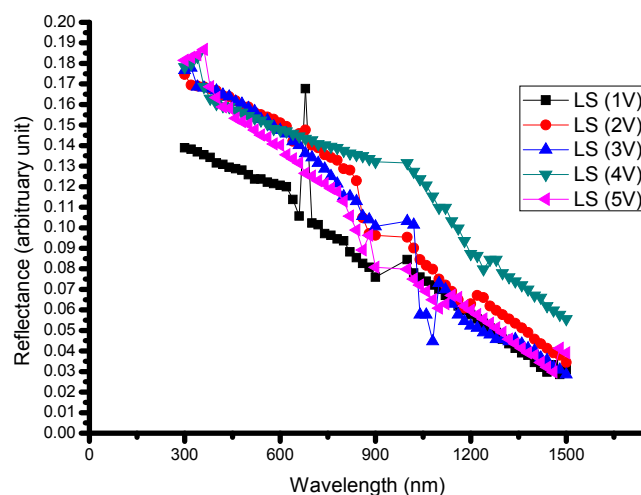
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Figure 2: plot of transmittance as a function wavelength

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120 Figure 3 shows the plot reflectance as a function of wavelength of PbS thin films deposited at
121 different potential at constant time (60s). From Fig. 3, it was observed that the wavelength of
122 incident radiation increases as the reflectance decreases. It was observed that sample
123 deposited at 5V recorded the highest reflectance value of 0.182 at incidence wavelength of
124 300nm in the infrared region and reflectance value of 0.041 in the ultraviolet region at
125 incidence wavelength of 1480nm. The sample deposited at 1V recorded the lowest
126 reflectance value of 0.139 at incidence wavelength of 300nm in the near infrared and
127 reflectance value of 0.030 at incidence wavelength of 1460nm at the ultraviolet region [12,
128 9-10].

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Figure 3: plot of reflectance as a function wavelength

Figure 4 shows refractive index as a function of photon energy of PbS thin films deposited at different potential at constant time (60s). From Fig. 4, it was observed that the refractive index increases as the photon energy increases. It was observed that sample deposited at 1V recorded the lowest refractive index of 0.14 with wavelength of 300nm, while sample deposited at 4V recorded the highest refractive index of 2.484 with photon energy value of 4.137. However, the refractive index increases moderately in both regions [12, 9-10].

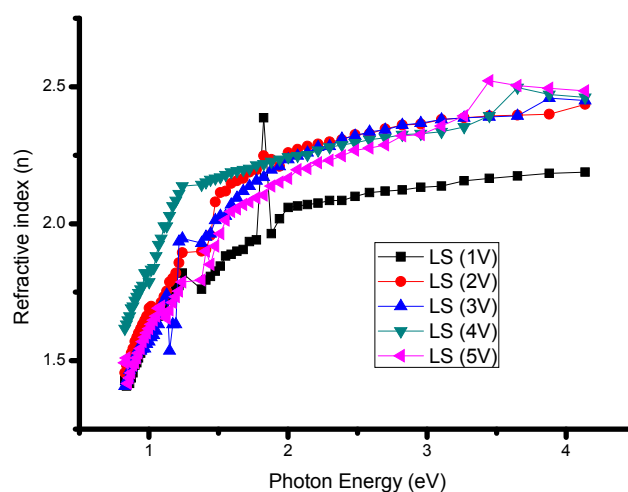


Figure 4: plot of refractive index as a function photon energy

Figure 5-6 shows the plot optical conductivity and extinction coefficient as a function of photon energy of PbS thin films deposited at different potential at constant time (60s). From the graph, it was observed that the optical conductivity and extinction coefficient increase as the photon energy increases [12, 9-10].

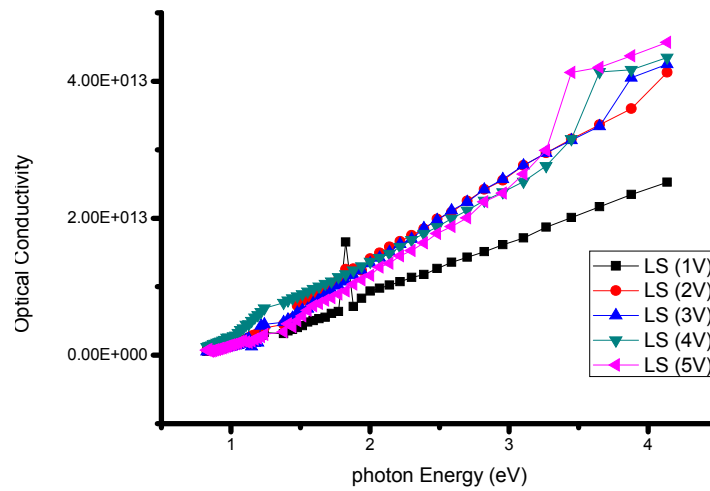


Figure 5: plot of optical conductivity as a function photon energy

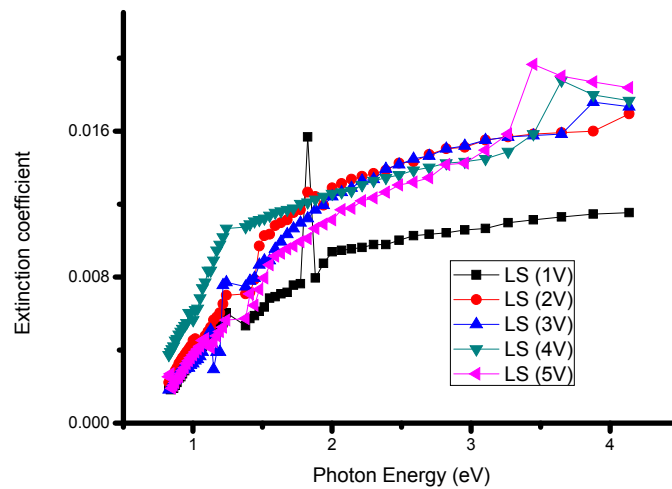


Figure 6: plot of extinction coefficient as a function photon energy

Figure 7-8 shows the plot real and imaginary dielectric constant as a function of photon energy of PbS thin films deposited at different potential at constant time (60s). From the graph, it was observed that the real and imaginary dielectric constant was increases the photon energy increases [12, 9-10].

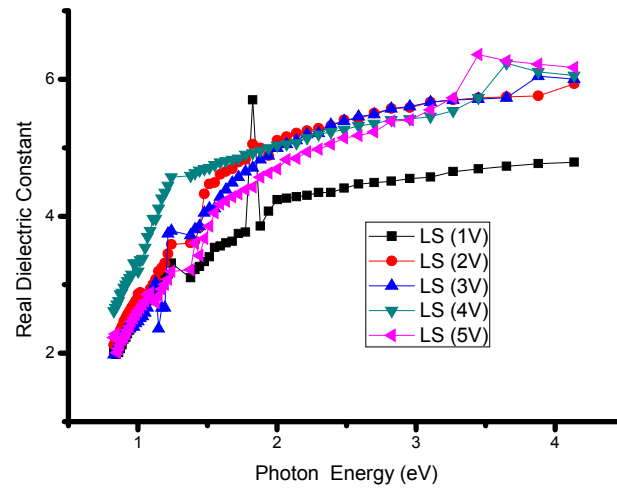


Figure 7: plot of real dielectric constant as a function photon energy

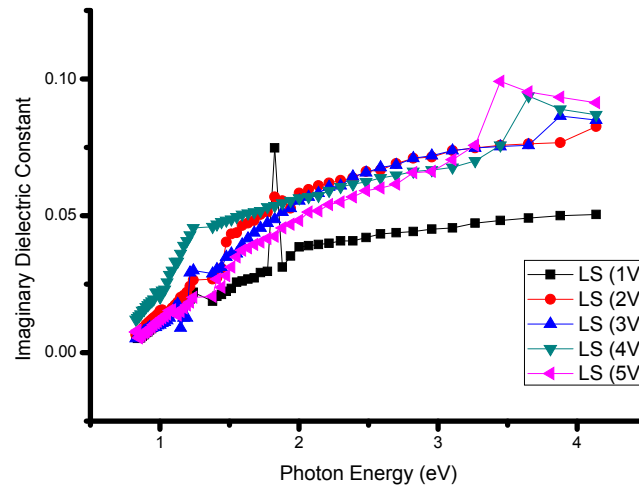


Figure 8: plot of imaginary dielectric constant as a function photon energy

The band gap energy and transition types were derived from mathematical processing of the data obtained from the optical absorbance versus photon energy with the following relationships for near edge absorption.

$$\alpha = n(h\nu - E_g)/2 \quad (1)$$

Where ν is the frequency, h is the Planck's constant, while n carries the value of either 1 or 4. The band gap E_g could be obtained from a straight line plot of α^2 as a function of $h\nu$; an

extrapolation of the value of α^2 to zero will give band gap. If a straight line graph is obtained from $n=1$, it indicates a direct transition between the states of the semiconductor, whereas the transition is indirect if a straight line graph is obtained from $n = 4$. The band gap energy of 1.7eV-2.4eV was obtained with a direct transition shows in figure 9 [12, 9-10]

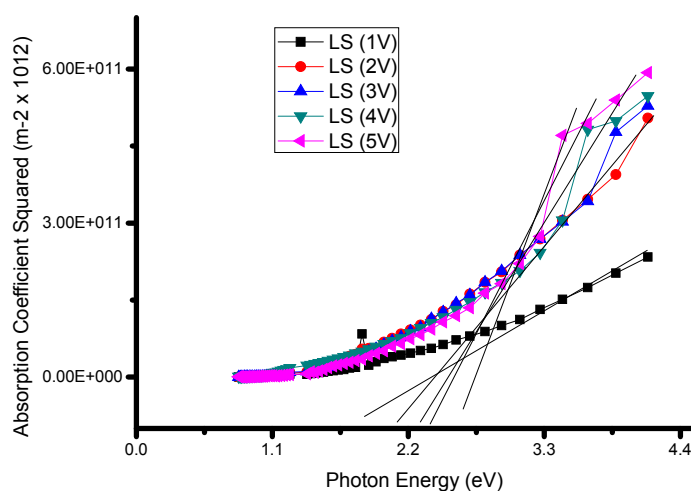


Figure 9: plot of absorption coefficient square as a function of photon energy

4.0 Conclusions

Electrodeposition techniques have been used to grown PbS thin films in this paper. It was observed that the thickness of the material as deposited depend on deposition potential. The resistivity and conductivity of the films increases as the thickness of the films increases. It was observed that as the absorbance decreases the wavelength of the films radiation increases. It was noticed that samples deposited at 5V recorded the value of 0.249 at a wavelength incidence of 360nm while Sample deposited at 1V was found to recorded lowest absorption value of 0.149 at incidence wavelength of 300nm. Sample deposited at 4V tend to maintain a steady increase which recorded the absorption value of 0.235 at incidence wavelength of 320nm. It was observed that the transmittance increases with the wavelength of incident radiation, it was noticed that all the samples deposited at different time interval followed the same tread. It was also observed that sample deposited at 1V recorded the highest transmittance of 0.716% in the infrared region at incidence wavelength of 300nm and transmittance of about 0.946% in the ultraviolet region at incidence wavelength of 1500nm, while sample deposited at 5V recorded the lowest transmittance. From the result

analysis it was observed that when the wavelength of incident radiation increases, the reflectance decreases. It was observed that sample deposited at 5V recorded reflectance value of 0.182 at incidence wavelength of 300nm in the infrared region and reflectance value of 0.041 in the ultraviolet region at incidence wavelength of 1480nm. Sample deposited at 1V recorded the reflectance value of 0.139 at incidence wavelength of 300nm in the near infrared and reflectance value of 0.030 at incidence wavelength of 1460nm at the ultraviolet region. From the result analysis it was observed that the refractive index, optical conductivity, extinction coefficient, real dielectric constant and imaginary dielectric constant were increased as the photon energy of the material was increased.

6.0 References

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